

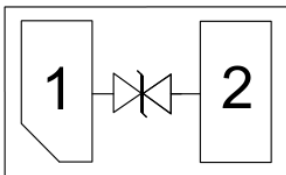
Features

- * Ultra small package: 1.0x0.6x0.5mm
- * Ultra low capacitance: 15pF typical
- * Ultra low leakage: nA level
- * Low operating voltage: 5V
- * Low clamping voltage
- * 2-pin leadless package
- * Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 8A (8/20 μs)
- * RoHS Compliant

Description

The ESD5451N is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive data and power line. The ESD5451N complies with the IEC 61000-4-2 (ESD) standard with $\pm 15\text{ kV}$ air and $\pm 8\text{ kV}$ contact discharge. It is assembled into an ultra-small 1.0x0.6x0.5mm lead-free 0402 package. The small size and high ESD surge protection make ESD5451N an ideal choice to protect cell phone, digital cameras, audio players and many other portable applications.

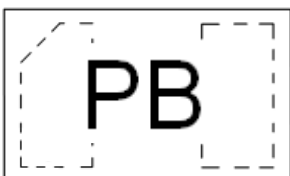
Circuit Diagram



Applications

- * Cellular Handsets and Accessories
- * Personal Digital Assistants
- * Notebooks and Handhelds
- * Portable Instrumentation
- * Digital Cameras
- * Peripherals
- * Audio Players
- * Keypads, Side Keys, LCD Displays

Package Outline



Transparent top view

PB: Device Marking Code

Ordering Information

Part Number	Packaging	Reel Size
ESD5451N	10000/Tape & Reel	7 inch

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

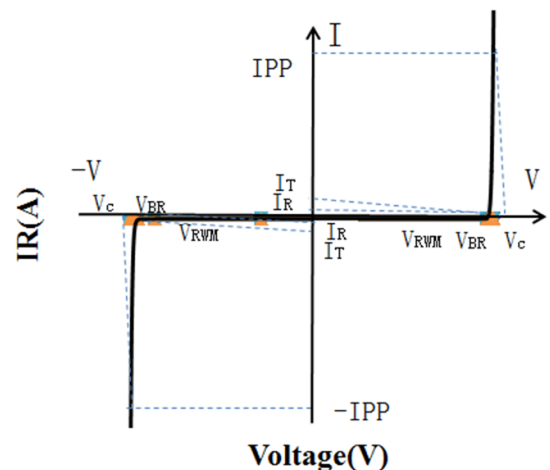
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	100	W
Peak Pulse Current (8/20 μs)	IPP	8	A
ESD per IEC 61000-4-2 (Air)	VESD	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	TJ	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	Tstg	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Working Voltage	V_{RWM}				5.0	V
Breakdown Voltage	V_{BR}	$I_{\text{T}} = 1\text{mA}$	6.0	6.5		V
Reverse Leakage Current	I_{R}	$V_{\text{RWM}} = 5.0\text{V}$			0.5	μA
Clamping Voltage	V_{C}	$I_{\text{PP}} = 1\text{A}$ (8 x 20 μs pulse)		7.0	8.0	V
Clamping Voltage	V_{C}	$I_{\text{PP}} = 8\text{A}$ (8 x 20 μs pulse)		9.0	13.0	V
Junction Capacitance	C_{J}	$V_{\text{R}} = 0\text{V}$, $f = 1\text{MHz}$		15	18	pF

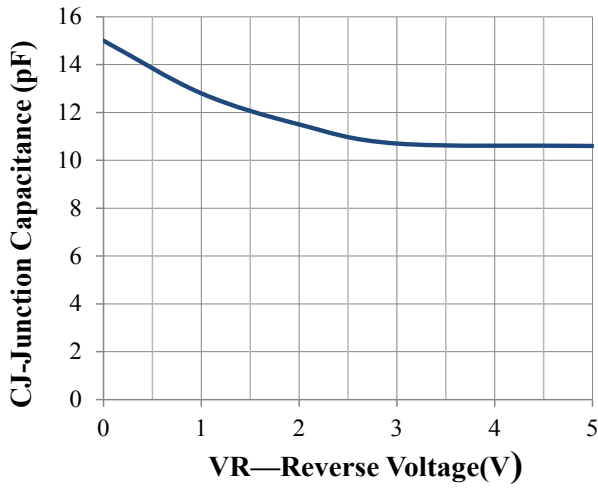
Portion Electronics Parameter

Symbol	Parameter
I_{T}	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_{C}	Clamping Voltage @ I_{C}

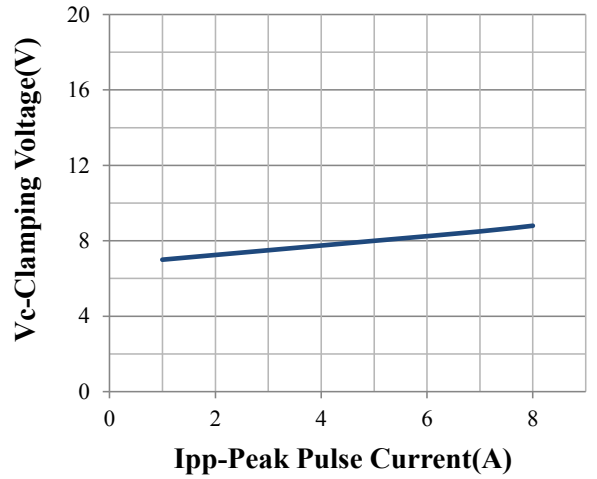




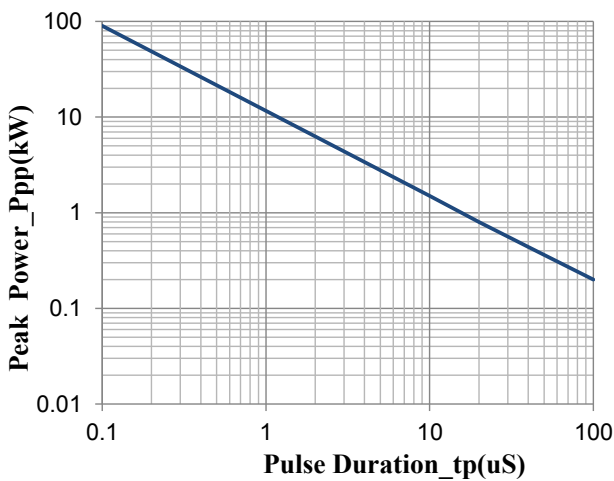
Typical Performance Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise Specified)



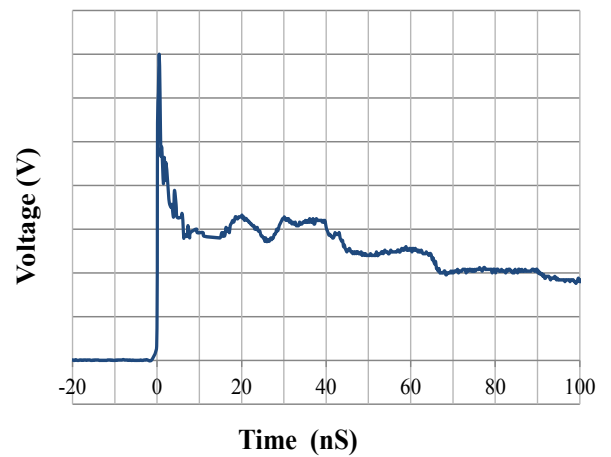
Junction Capacitance vs. Reverse Voltage



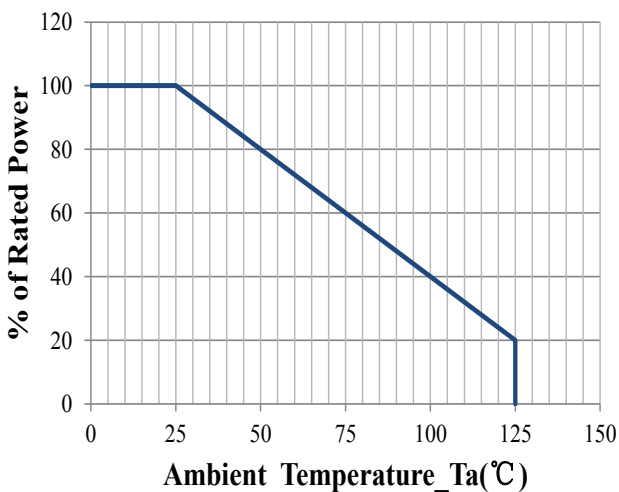
Clamping Voltage vs. Peak Pulse Current



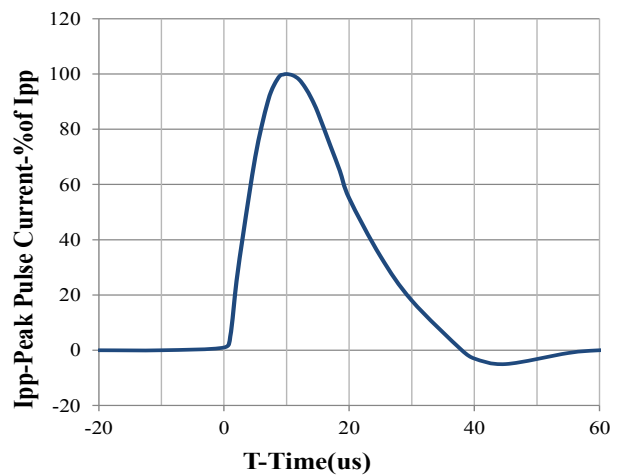
Peak Pulse Power vs. Pulse Time



IEC61000-4-2 Pulse Waveform

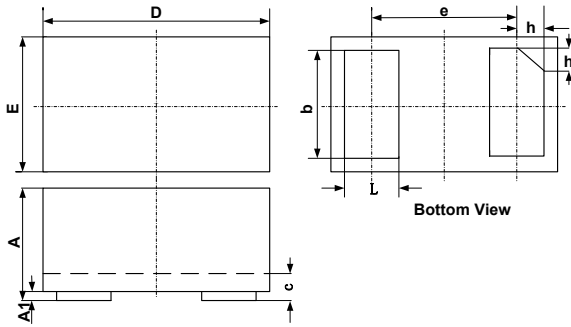


Power Derating Curve



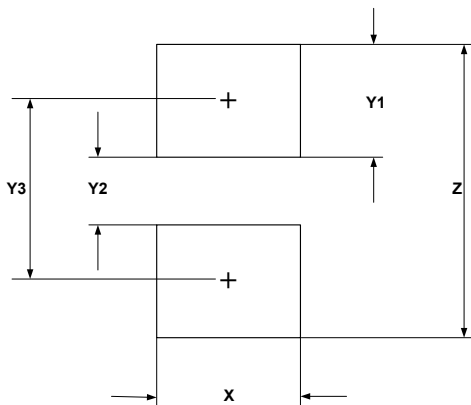
8 X 20us Pulse Waveform

DFN1006-2(0402)Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
L	0.20	0.25	0.30	0.008	0.010	0.012
h	0.07	0.12	0.17	0.003	0.005	0.007

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.60	0.024
Y1	0.50	0.020
Y2	0.30	0.012
Y3	0.80	0.032
Z	1.30	0.052